

REMARKS

Reconsideration of this application, as amended, is respectfully requested. Claim 1 has been amended to recite features formerly found in claim 5 and to clarify that the cleaning gas distribution channel is separate from the showerhead, which is used to introduce process gasses to the CVD chamber. No new matter is added by these amendments. See, e.g., Specification at paragraph 12.

Claim 1, as amended, is patentable over the combination of van Os, US 5,792,272 and Kholodenko, US 6,185,839. For example, neither of these references teach or suggest a chemical vapor deposition system with a showerhead fluidly coupled to processing gas plumbing for introducing processing gasses to the chemical vapor deposition chamber separately from a cleaning gas distribution channel, which is separate from the showerhead, as recited in claim 1.

The van Os reference describes a reactor chamber with two separate gas injection manifolds (e.g., See van Os, element 15 of FIG's. 1, 3a-c; and element 17 of FIG's 1 and 4). Both gas injection manifolds are used to deliver processing gases as well as cleaning gases into the plasma and processing chambers. The Kholodenko reference discloses pairs of process gas injection nozzles positioned at inclined angles for introducing a process gas to a reaction chamber.

Even if one were to modify the teachings of van Os with the arrangement of gas injection nozzles described by Kholodenko, one would not arrive at the present invention because there would still not be separate plumbing installations for processing gasses and cleaning gasses as recited in claim 1. Hence, the claims are patentable over this combination of references.

If there are any additional fees due in connection with this communication, please charge Deposit Account No. 19-3140.

Respectfully submitted,
SONNENSCHN NATH & ROSENTHAL LLP

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/Tarek N. Fahmi/

Tarek N. Fahmi

Reg. No. 41,402

P.O. Box 061080
Wacker Drive Station
Scars Tower
Chicago, IL 60606-1080
(650) 798-0320